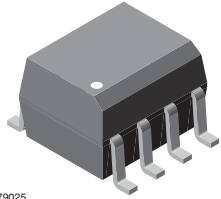
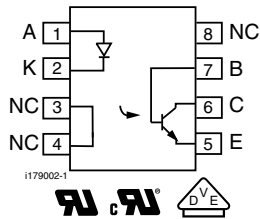


Optocoupler, Phototransistor Output, with Base Connection in SOIC-8



i179025



FEATURES

- Isolation test voltage, 4000 V_{RMS}
- Industry standard SOIC-8 surface mountable package
- Compatible with dual wave, vapor phase and IR reflow soldering
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

The IL211AT, IL212AT, IL213AT are optically coupled pairs with a gallium arsenide infrared LED and silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output.

The IL211AT, IL212AT, IL213AT comes in a standard SOIC-8 small outline package for surface mounting which makes it ideally suited for high density applications with limited space. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

A choice of 20 %, 50 %, and 100 % minimum CTR at I_F = 10 mA makes these optocouplers suitable for a variety of different applications.

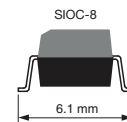
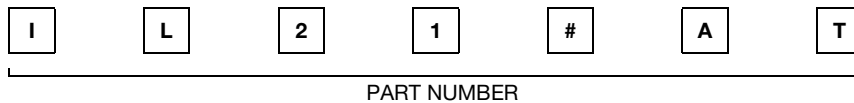
AGENCY APPROVALS

- UL1577, file no. E52744 system code Y
- cUL - file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-2 (VDE 0884) ⁽¹⁾
- DIN EN 60747-5-5 (pending) ⁽¹⁾

Note

⁽¹⁾ Available upon request, as option 1

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)		
	10 mA		
UL, cUL	> 20	> 50	> 100
SIOC-8	IL211AT	IL212AT	IL213AT

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Peak reverse voltage		V _R	6	V
Forward continuous current		I _F	60	mA
Power dissipation		P _{diss}	90	mW
Derate linearly from 25 °C			1.2	mW/°C
OUTPUT				
Collector emitter breakdown voltage		BV _{CEO}	30	V
Emitter collector breakdown voltage		BV _{ECO}	7	V
Collector base breakdown voltage		V _{CBO}	70	V
I _C MAX DC		I _C MAX DC	50	mA
I _C MAX	t < 1 ms	I _C MAX	100	mA
Power dissipation		P _{diss}	150	mW
Derate linearly from 25 °C			2	mW/°C

IL211AT, IL212AT, IL213AT



Vishay Semiconductors Optocoupler, Phototransistor Output,
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ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
COUPLER				
Isolation test voltage		V_{ISO}	4000	V_{RMS}
Total package dissipation	LED and detector	P_{tot}	240	mW
Derate linearly from 25 $^{\circ}\text{C}$			3.2	mW/ $^{\circ}\text{C}$
Storage temperature		T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Operating temperature		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Soldering time	at 260 $^{\circ}\text{C}$		10	s

Note

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 10\text{ mA}$		V_F		1.3	1.5	V
Reverse current	$V_R = 6\text{ V}$		I_R		0.1	100	μA
Capacitance	$V_R = 0\text{ V}$		C_O		13		pF
OUTPUT							
Collector emitter breakdown voltage	$I_C = 10\text{ }\mu\text{A}$		BV_{CEO}	30			V
Emitter collector breakdown voltage	$I_E = 10\text{ }\mu\text{A}$		BV_{ECO}	7			V
Collector dark current	$V_{CE} = 10\text{ V}$		I_{CEO}		5	50	nA
Collector emitter capacitance	$V_{CE} = 0\text{ V}$		C_{CE}		10		pF
COUPLER							
Saturation voltage, collector emitter	$I_F = 10\text{ mA}$		V_{CEsat}			0.4	V
Isolation test voltage	1 s		V_{ISO}	4000			V_{RMS}
Capacitance (input to output)			C_{IO}		0.5	50	pF
Resistance (input to output)			R_{IO}		100		G Ω
Collector emitter breakdown voltage	$I_C = 10\text{ }\mu\text{A}$		BV_{CEO}	30			V

Note

- Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	IL211AT	CTR	20	50		%
		IL212AT	CTR	50	80		%
		IL213AT	CTR	100	130		%

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Switching time	$I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, $V_{CC} = 10\text{ V}$		t_{on} , t_{off}		3		μs



IL211AT, IL212AT, IL213AT

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SAFETY AND INSULATION RATINGS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
V_{IOTM}			6000			V
V_{IORM}			560			V
P_{SO}					350	mW
I_{SI}					150	mA
T_{SI}					165	°C
Creepage distance			4			mm
Clearance distance			4			mm
Insulation thickness			0.2			mm

Note

- As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for “Safe Electrical Insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ °C}$, unless otherwise specified)

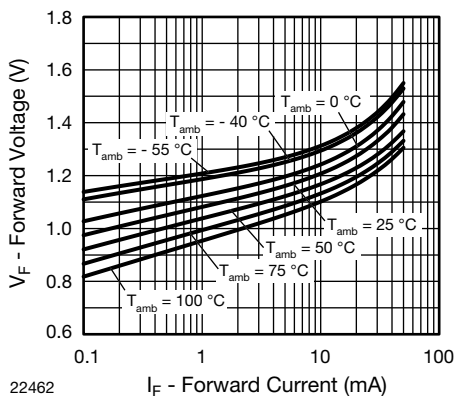


Fig. 1 - Forward Voltage vs. Forward Current

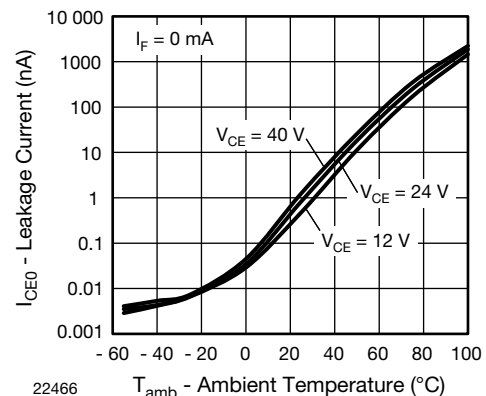


Fig. 3 - Leakage Current vs. Ambient Temperature

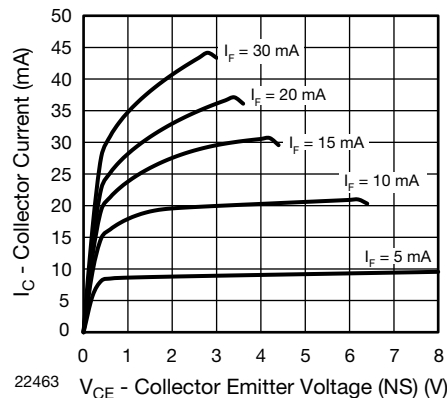


Fig. 2 - Collector Current vs. Collector Emitter Voltage (NS)

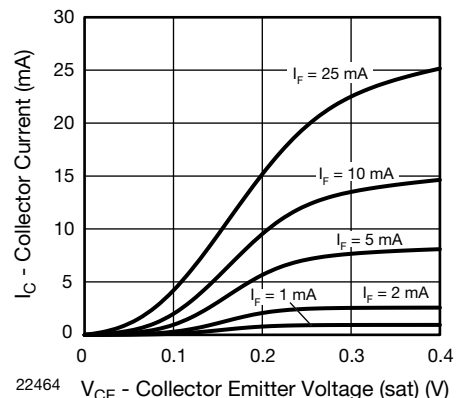


Fig. 4 - Collector Current vs. Collector Emitter Voltage (sat)

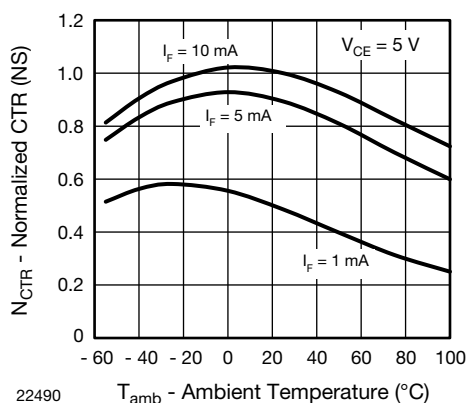


Fig. 5 - Normalized CTR (NS) vs. Ambient Temperature

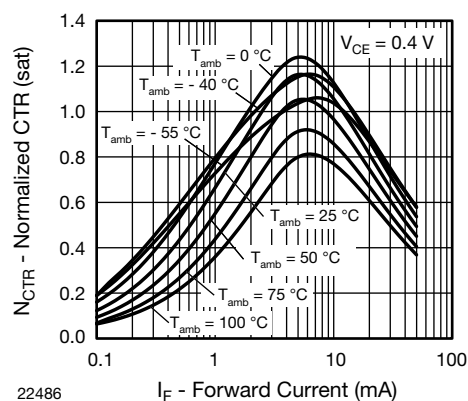


Fig. 8 - Normalized CTR (sat) vs. Forward Current

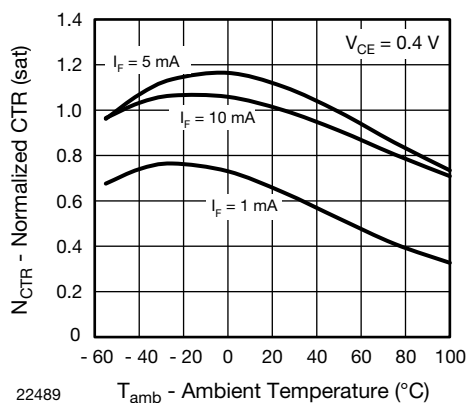


Fig. 6 - Normalized CTR (sat) vs. Ambient Temperature

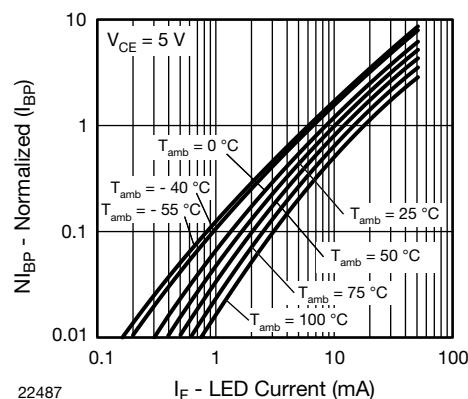


Fig. 9 - Normalized Photocurrent vs. LED Current

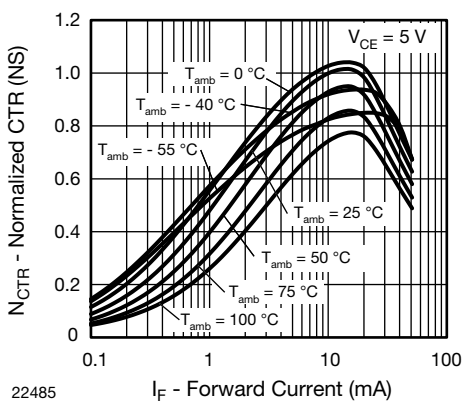


Fig. 7 - Normalized CTR (NS) vs. Forward Current

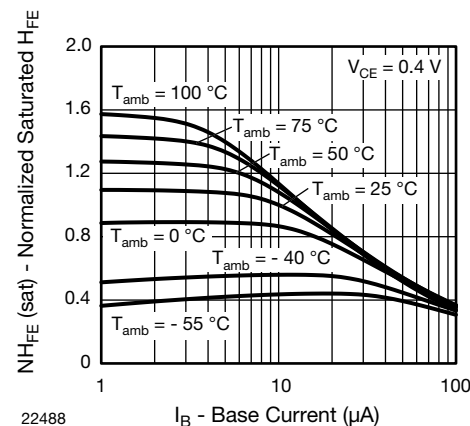


Fig. 10 - Normalized Saturated H_{FE} vs. Base Current

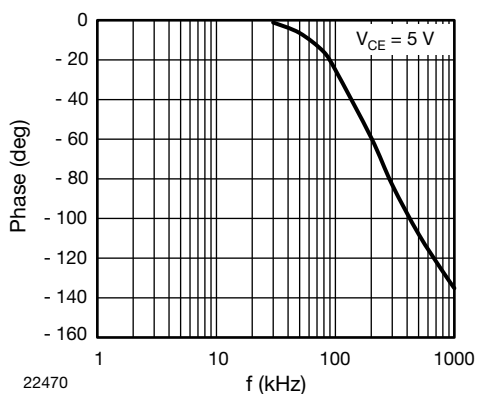


Fig. 11 - F_{CTR} vs. Phase Angle

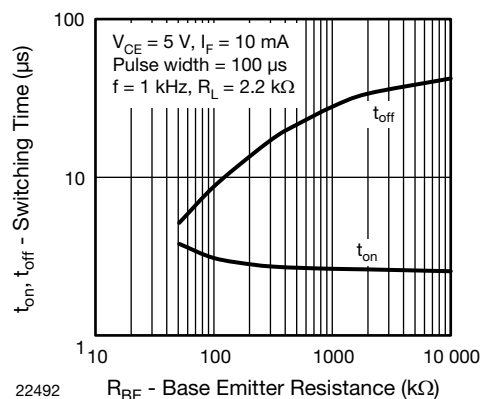


Fig. 14 - Switching Time vs. Base Emitter Resistance

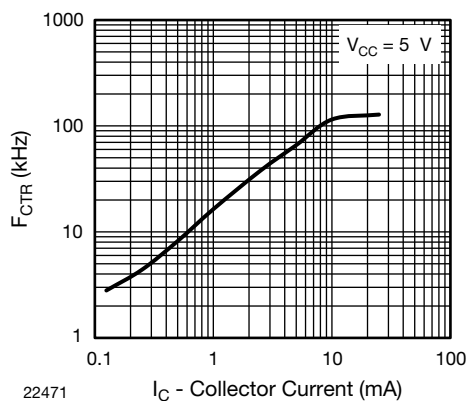


Fig. 12 - F_{CTR} vs. I_C

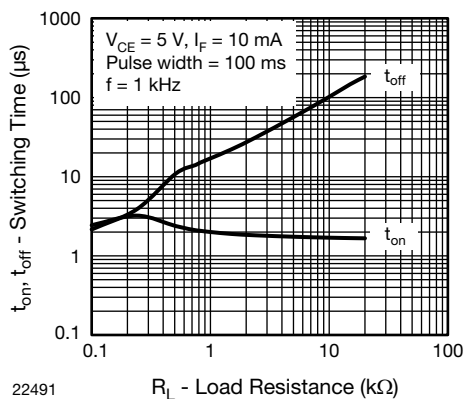


Fig. 13 - Switching Time vs. Load Resistance

Vishay Semiconductors Optocoupler, Phototransistor Output,
with Base Connection in SOIC-8 Package



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